

# DCR780G30

## **Phase Control Thyristor**

DS6045-1 April 2011 (LN28256)

#### **FEATURES**

- Double Side Cooling
- High Surge Capability

#### **APPLICATIONS**

- High Power Drives
- High Voltage Power Supplies
- Static Switches

#### **VOLTAGE RATINGS**

Part and Ordering Number	Repetitive Peak Voltages V <sub>DRM</sub> and V <sub>RRM</sub> V	Conditions
DCR780G30 DCR780G28 DCR780G26 DCR780G24	3000 2800 2600 2400	$\begin{array}{l} T_{v_j} = -40^{\circ}C \ to \ 125^{\circ}C, \\ I_{DRM} = I_{RRM} = 60mA, \\ V_{DRM}, \ V_{RRM} \ t_p = 10ms, \\ V_{DSM} \& \ V_{RSM} = \\ V_{DRM} \& \ V_{RRM} \ +100V \\ respectively \end{array}$

Lower voltage grades available.

### **ORDERING INFORMATION**

When ordering, select the required part number shown in the Voltage Ratings selection table.

For example:

#### DCR780G30

Note: Please use the complete part number when ordering and quote this number in any future correspondence relating to your order.

#### **KEY PARAMETERS**

V <sub>DRM</sub>	3000 V
I <sub>T(AV)</sub>	780 A
I <sub>TSM</sub>	10500 A
dV/dt*	1000 V/µs
dl/dt	200 A/µs

#### \* Higher dV/dt selections available

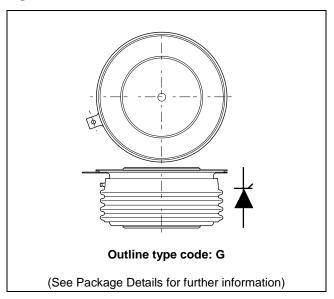


Fig. 1 Package outline



#### **CURRENT RATINGS**

 $T_{case} = 60^{\circ}C$  unless stated otherwise

Symbol	Parameter	Test Conditions		Units	
Double Si	Double Side Cooled				
I <sub>T(AV)</sub>	Mean on-state current	Half wave resistive load	780	А	
I <sub>T(RMS)</sub>	RMS value	-	1220	А	
Ι <sub>Τ</sub>	Continuous (direct) on-state current	-	1100	А	

#### SURGE RATINGS

Symbol	Parameter	Test Conditions	Max.	Units
I <sub>TSM</sub>	Surge (non-repetitive) on-state current	ent 10ms half sine, $T_{case} = 125^{\circ}C$		kA
l <sup>2</sup> t	I <sup>2</sup> t for fusing	$V_R = 0$	0.551	MA <sup>2</sup> s

#### THERMAL AND MECHANICAL RATINGS

Symbol	Parameter	Test Conditions		Min.	Max.	Units
R <sub>th(j-c)</sub>	Thermal resistance – junction to case	Double side cooled	DC	-	0.035	°C/W
R <sub>th(c-h)</sub>	Thermal resistance – case to heatsink	Double side cooled	DC	-	0.008	°C/W
$T_{vj}$	Virtual junction temperature	Blocking V <sub>DRM</sub> / <sub>VRRM</sub>		-	125	°C
T <sub>stg</sub>	Storage temperature range			-40	140	°C
F <sub>m</sub>	Clamping force			12	18	kN



### **DYNAMIC CHARACTERISTICS**

Symbol	Parameter	Test Conditions		Min.	Max.	Units
I <sub>RRM</sub> /I <sub>DRM</sub>	Peak reverse and off-state current	At V <sub>RRM</sub> /V <sub>DRM</sub> , T <sub>case</sub> = 125°C		-	60	mA
dV/dt	Max. linear rate of rise of off-state voltage	To 67% $V_{DRM}$ , $T_j = 125$ °C, gate open		1000	-	V/µs
dl/dt	Rate of rise of on-state current	From 67% V <sub>DRM</sub> to 1000A Repetitive 50Hz		-	200	A/µs
		Gate source 30V, $10\Omega$ ,	Non-repetitive	-	1000	A/µs
		t <sub>r</sub> < 0.5µs, T <sub>j</sub> = 125°C				
V <sub>T</sub>	On-state voltage	I <sub>T</sub> = 1500A, T <sub>case</sub> = 125°C			1.90	V
V <sub>T(TO)</sub>	Threshold voltage – Low level	T <sub>case</sub> = 125°C		-	1.00	V
r <sub>T</sub>	On-state slope resistance – Low level	T <sub>case</sub> = 125°C		-	0.60	mΩ
t <sub>gd</sub>	Delay time	$V_D$ = 67% $V_{DRM}$ , gate source 30V, 10 $\Omega$ $t_r$ = 0.5µs, $T_j$ = 25°C		-	3.0	μs
tq	Turn-off time	$T_{j} = 125^{\circ}C, V_{R} = 100V, dl/dt = 10A/\mu s,$ $dV_{DR}/dt = 20V/\mu s \text{ linear to } 67\% V_{DRM}$			400	μs
				-		
Qs	Stored charge	I <sub>T</sub> = 1000A, tp = 1000us,T <sub>j</sub> = 125°C, dl/dt =10A/μs,		-	2400	μC
I <sub>RR</sub>	Reverse recovery current			-	125	А
١L	Latching current	T <sub>j</sub> = 25°C,		-	1	А
I <sub>H</sub>	Holding current	T <sub>j</sub> = 25°C,		-	200	mA

### GATE TRIGGER CHARACTERISTICS AND RATINGS

Symbol	Parameter	Test Conditions	Max.	Units
V <sub>GT</sub>	Gate trigger voltage	$V_{DRM} = 5V, T_{case} = 25^{\circ}C$	3	V
V <sub>GD</sub>	Gate non-trigger voltage	At 40% V <sub>DRM</sub> , T <sub>case</sub> = 125°C	TBD	V
I <sub>GT</sub>	Gate trigger current	$V_{DRM} = 5V, T_{case} = 25^{\circ}C$	300	mA
I <sub>GD</sub>	Gate non-trigger current	At 40% V <sub>DRM</sub> , T <sub>case</sub> = 125°C	TBD	mA



### CURVES

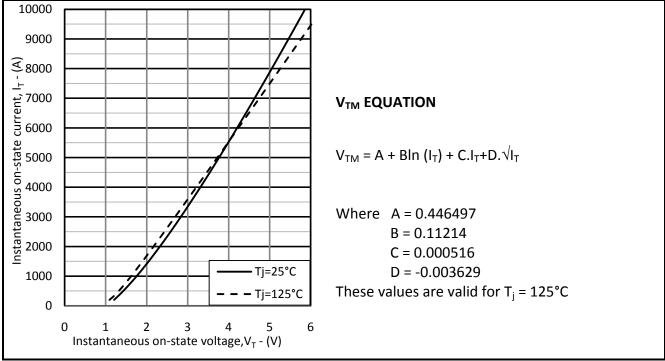


Fig.2 Maximum & minimum on-state characteristics

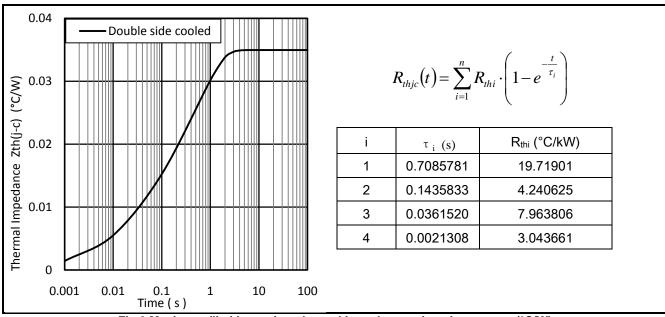
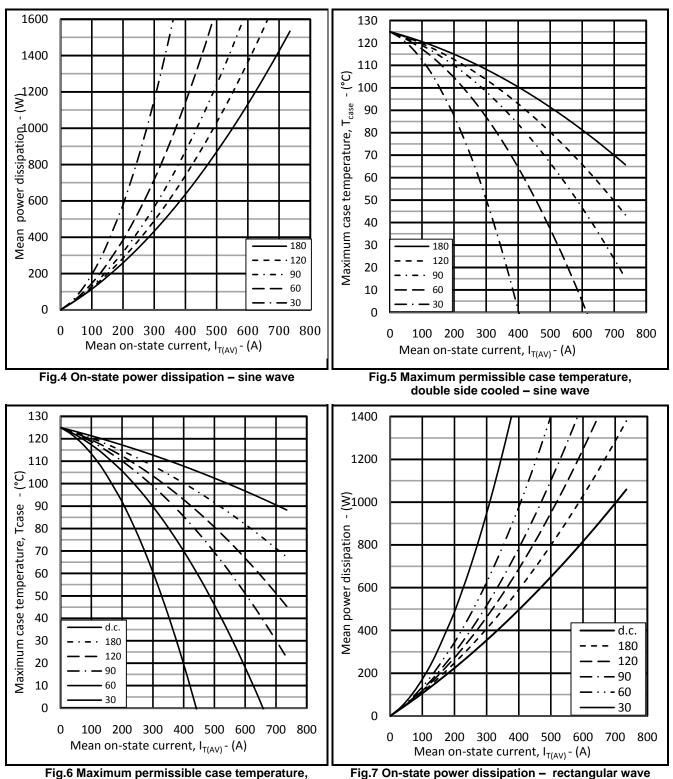


Fig.3 Maximum (limit) transient thermal impedance – junction to case (°C/W)





double side cooled - rectangular wave





#### DCR780G30

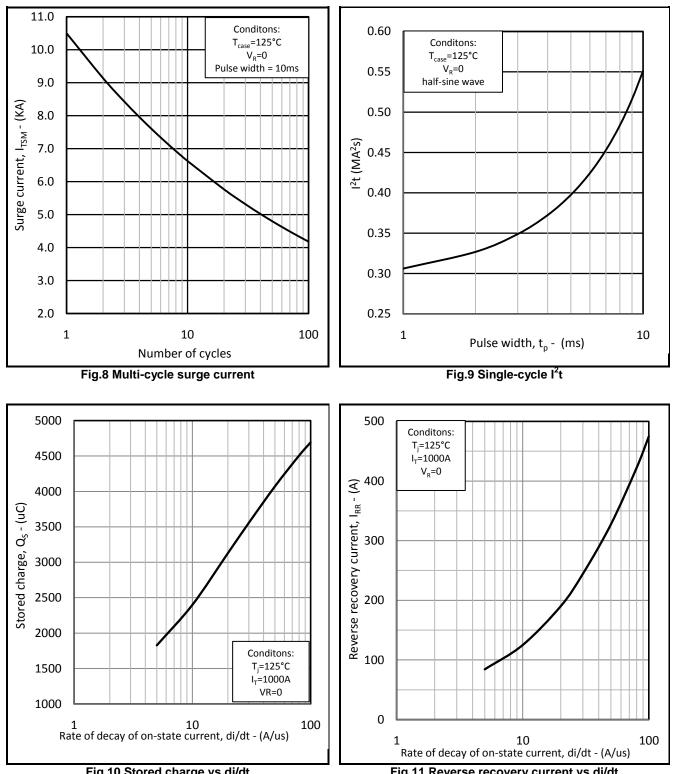
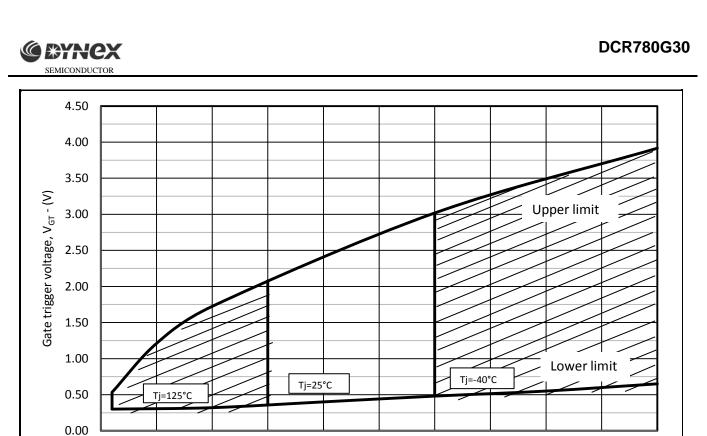


Fig.10 Stored charge vs di/dt

Fig.11 Reverse recovery current vs di/dt



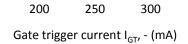
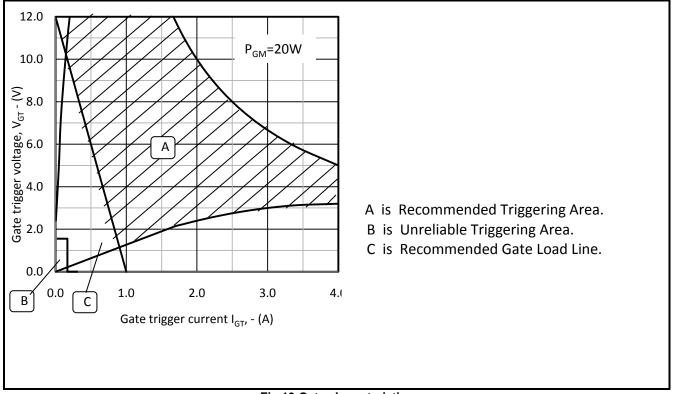


Fig.12 Gate characteristics



#### Fig.13 Gate characteristics



#### PACKAGE DETAILS

For further package information, please contact Customer Services. All dimensions in mm, unless stated otherwise. DO NOT SCALE.

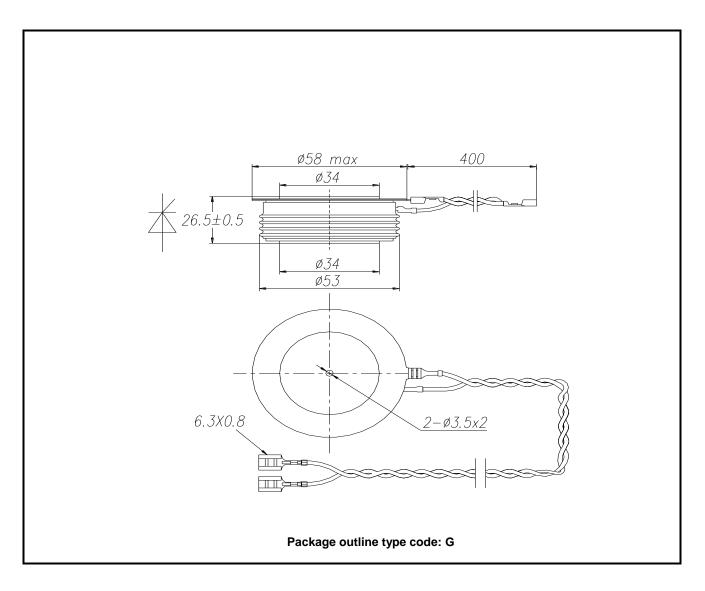


Fig.14 Package outline



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